

MOS FIELD EFFECT TRANSISTOR $\mu PA2708GR$

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The μ PA2708GR is N-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of notebook computer.

FEATURES

- Low on-state resistance
- $\begin{aligned} R_{DS(on)1} &= 5.5 \text{ m}\Omega \text{ MAX.} \text{ (V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 9.0 \text{ A}) \\ R_{DS(on)2} &= 7.5 \text{ m}\Omega \text{ MAX.} \text{ (V}_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 9.0 \text{ A}) \end{aligned}$
- Low Ciss: Ciss = 4700 pF TYP. (VDs = 10 V, VGs = 0 V)
- Small and surface mount package (Power SOP8)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA2708GR-E1	Power SOP8
μPA2708GR-E2	Power SOP8
μ PA2708GR-E1-A ^{Note}	Power SOP8
μ PA2708GR-E2-A ^{Note}	Power SOP8

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC)	D(DC)	±17	А
Drain Current (pulse) Note1	D(pulse)	±68	А
Total Power Dissipation Note2	P T1	1.1	W
Total Power Dissipation (PW =10 sec) ^{Note2}	Pt2	2.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	–55 to +150	°C
Single Avalanche Current Note3	las	17	А
Single Avalanche Energy Note3	Eas	28.9	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- 2. Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm
- 3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω , L = 100 μ H, V_{GS} = 20 \rightarrow 0 V

THERMAL RESISTANCE

Channel to Ambient Note	Rth(ch-A)	114	°C/W
Channel to Drain Lead ^{Note}	Rth(ch-L)	30	°C/W

Note Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm

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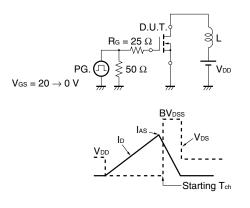
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	lgss	V_{GS} = ±20 V, V_{DS} = 0 V			±100	nA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.0		2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 9.0 A	10			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 9.0 A		4.5	5.5	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 9.0 A		5.6	7.5	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		4700		pF
Output Capacitance	Coss	V _{GS} = 0 V		670		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		340		pF
Turn-on Delay Time	td(on)	V _{DD} = 15 V, I _D = 9.0 A		19		ns
Rise Time	tr	V _{GS} = 10 V		26		ns
Turn-off Delay Time	td(off)	Rg = 10 Ω		100		ns
Fall Time	tr			27		ns
Total Gate Charge	QG	V _{DD} = 15 V		38		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 5 V		13		nC
Gate to Drain Charge	Qgd	I _D = 17 A		12		nC
Body Diode Forward Voltage Note	VF(S-D)	IF = 17 A, VGS = 0 V		0.8		V
Reverse Recovery Time	trr	IF = 17 A, VGS = 0 V		33		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/ <i>µ</i> s		27		nC
Gate Resistance	Rg	f = 1 MHz		1.2		Ω

ELECTRICAL CHARACTERISTICS (T_A = 25°C, All terminals are connected.)

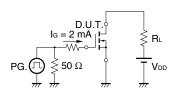
Note Pulsed

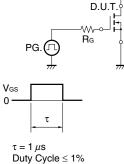
TEST CIRCUIT 1 AVALANCHE CAPABILITY

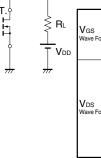
TEST CIRCUIT 2 SWITCHING TIME

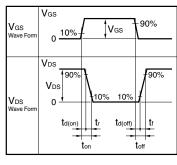


TEST CIRCUIT 3 GATE CHARGE

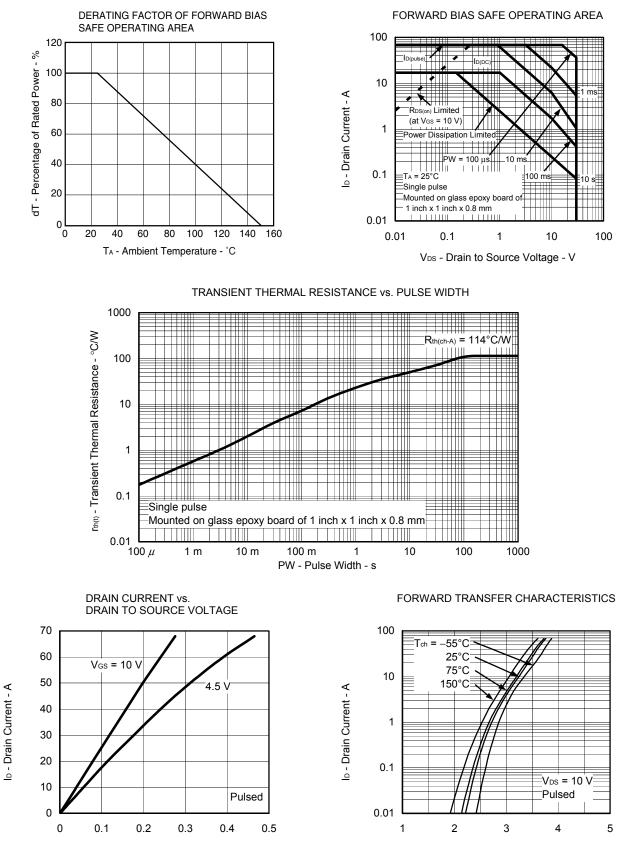






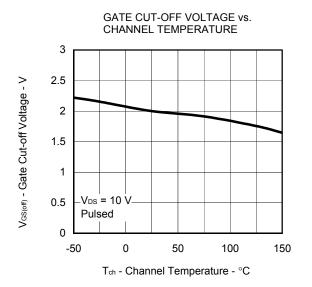


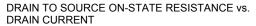
TYPICAL CHARACTERISTICS (TA = 25^{\circ}C)

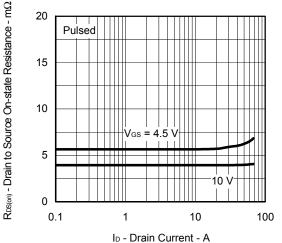


VGS - Gate to Source Voltage - V

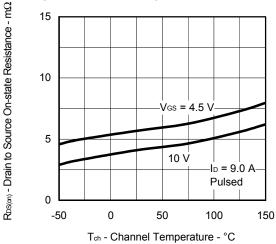
VDS - Drain to Source Voltage - V



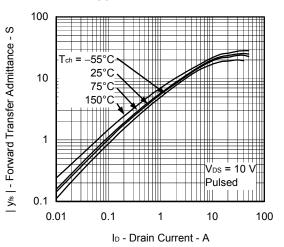




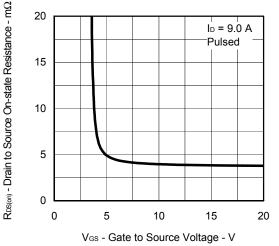




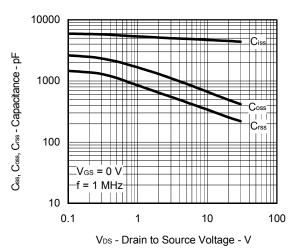
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



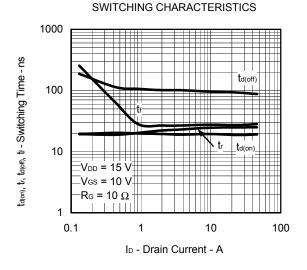
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



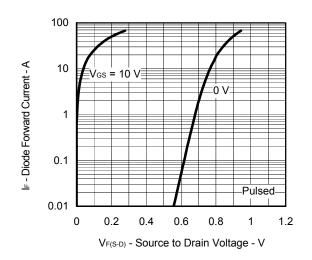
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

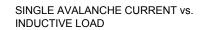


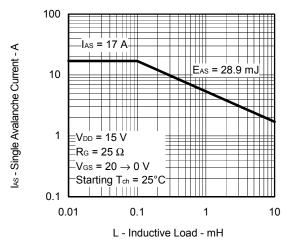




SOURCE TO DRAIN DIODE FORWARD VOLTAGE

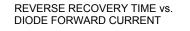


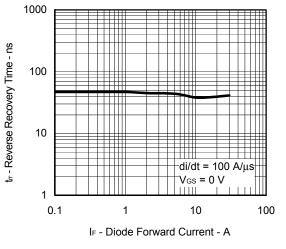


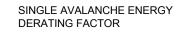


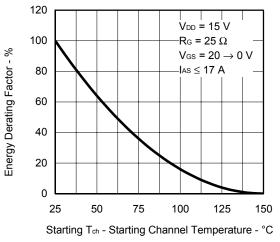
VDD = 24 V V_{DS} - Drain to Source Voltage - V V_{GS} - Gate to Source Voltage - V 6 V VDS QG - Gate Charge - nC

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



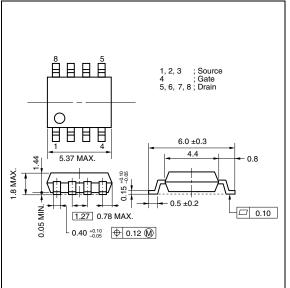




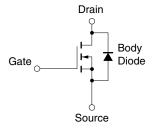


PACKAGE DRAWING (Unit: mm)

Power SOP8



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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